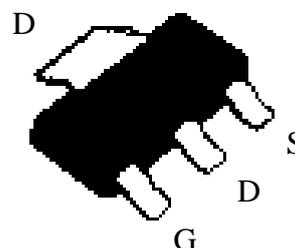


## P-Channel Logic Level Enhancement Mode Power MOSFET

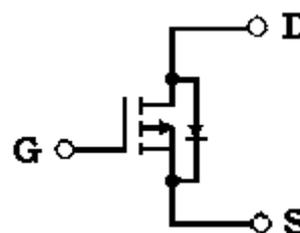
### Features:

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating & halogen-free package

SOT-223



$BV_{DSS}$	-200V
$I_D @ V_{GS} = -10V, T_A = 25^\circ C$	-1.2A
$R_{DS(on)} @ V_{GS} = -10V, I_D = -1A$	0.80Ω (typ)
$R_{DS(on)} @ V_{GS} = -6V, I_D = -0.5A$	0.85Ω (typ)



G : Gate D : Drain S :  
Source

### Ordering Information

Device	Package	Shipping
KLEJ0P20	SOT-223 (Pb-free lead plating and halogen-free package)	2500 pcs / tape & reel

**Absolute Maximum Ratings** (T<sub>C</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V <sub>DS</sub>	-200	V
Gate-Source Voltage	V <sub>GS</sub>	±30	
Continuous Drain Current @ V <sub>GS</sub> =-10V, T <sub>C</sub> =25°C	I <sub>D</sub>	-1.6	A
Continuous Drain Current @ V <sub>GS</sub> =-10V, T <sub>C</sub> =100°C		-1	
Continuous Drain Current @ V <sub>GS</sub> =-10V, T <sub>A</sub> =25°C		-1.2	
Continuous Drain Current @ V <sub>GS</sub> =-10V, T <sub>A</sub> =70°C		-0.96	
Pulsed Drain Current *1	I <sub>DM</sub>	-6.4	
Avalanche Current	I <sub>AS</sub>	-1.6	
Avalanche Energy @ L=10mH, I <sub>D</sub> =-1.6A, R <sub>G</sub> =25Ω	E <sub>AS</sub>	13	mJ
Repetitive Avalanche Energy @ L=0.05mH *2	E <sub>AR</sub>	2	
Total Power Dissipation @T <sub>A</sub> =25°C	P <sub>d</sub>	2.5	W
Total Power Dissipation @T <sub>A</sub> =100°C		1	
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55~+150	°C

Note : \*1. Pulse width limited by maximum junction temperature  
 \*2. Duty cycle ≤ 1%

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R <sub>th,j-c</sub>	25	°C/W
Thermal Resistance, Junction-to-ambient, max	R <sub>th,j-a</sub>	50 (Note)	

Note : Surface mounted on a 1 in<sup>2</sup> pad of 2 oz. copper, t≤10s; 110 °C/W when mounted on minimum copper pad.

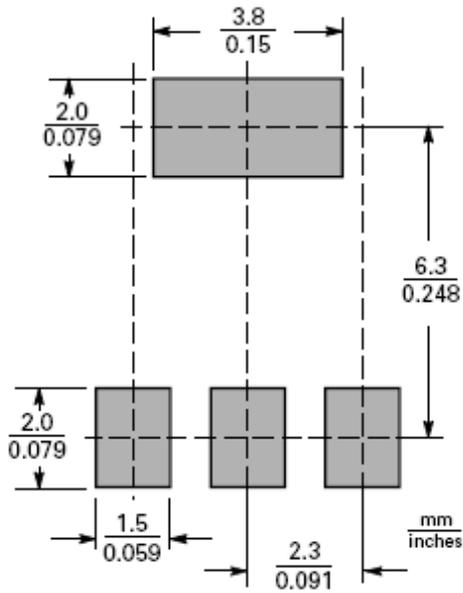
**Characteristics (T<sub>C</sub>=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	-200	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA
V <sub>GS(th)</sub>	-2	-	-4		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±30, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> =-160V, V <sub>GS</sub> =0V
	-	-	-25		V <sub>DS</sub> =-160V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C
R <sub>DS(ON)</sub> *1	-	0.80	1.0	Ω	V <sub>GS</sub> =-10V, I <sub>D</sub> =-1A
	-	0.85	1.1		V <sub>GS</sub> =-6V, I <sub>D</sub> =-0.5A
G <sub>FS</sub> *1	-	2	-	S	V <sub>DS</sub> =-5V, I <sub>D</sub> =-0.5A
<b>Dynamic</b>					
Q <sub>g</sub> *1, 2	-	14	-	nC	I <sub>D</sub> =-1A, V <sub>DS</sub> =-160V, V <sub>GS</sub> =-10V
Q <sub>gs</sub> *1, 2	-	4	-		
Q <sub>gd</sub> *1, 2	-	4.8	-		
t <sub>d(ON)</sub> *1, 2	-	8	-	ns	V <sub>DS</sub> =-100V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω
t <sub>r</sub> *1, 2	-	4	-		
t <sub>d(OFF)</sub> *1, 2	-	22	-		
t <sub>f</sub> *1, 2	-	6	-		

Ciss	-	812	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =-25V, f=1MHz
Coss	-	37	-		
Crss	-	18	-		
<b>Source-Drain Diode</b>					
I <sub>S</sub> *1	-	-	-1.6	A	
I <sub>SM</sub> *3	-	-	-6.4		
V <sub>SD</sub> *1	-	-0.8	-1.2	V	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V
trr	-	80	-	ns	I <sub>F</sub> =-1A, dI <sub>F</sub> /dt=100A/μs
Qrr	-	100	-	nC	

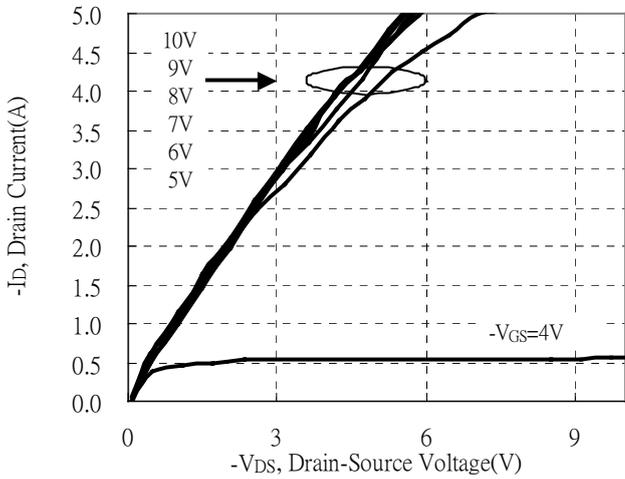
Note : \*1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%  
 \*2.Independent of operating temperature  
 \*3.Pulse width limited by maximum junction temperature.

**Recommended soldering footprint**

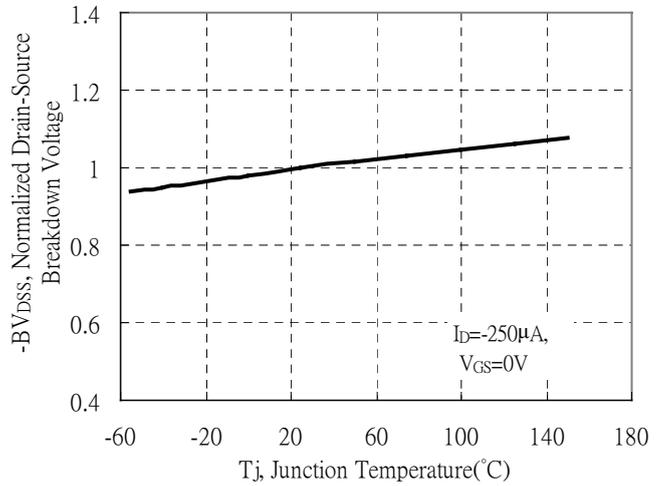


### Typical Characteristics

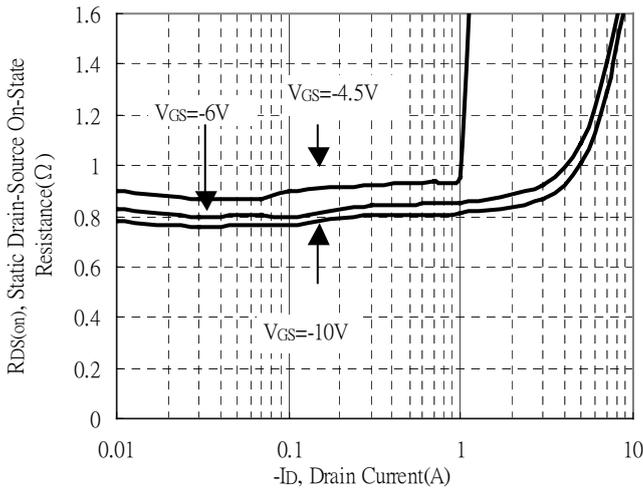
Typical Output Characteristics



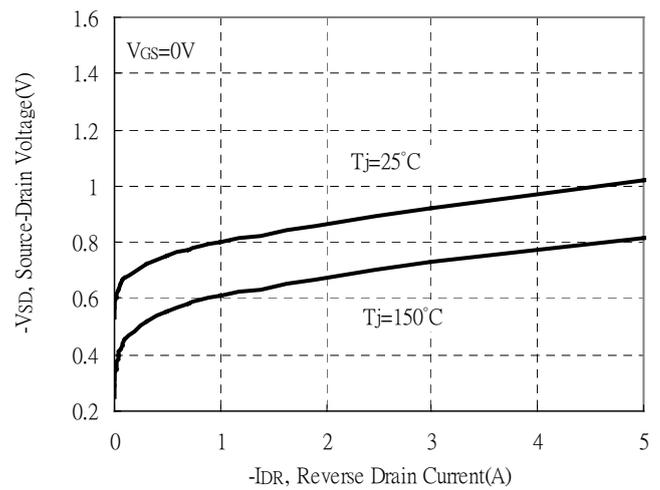
Brekdown Voltage vs Ambient Temperature



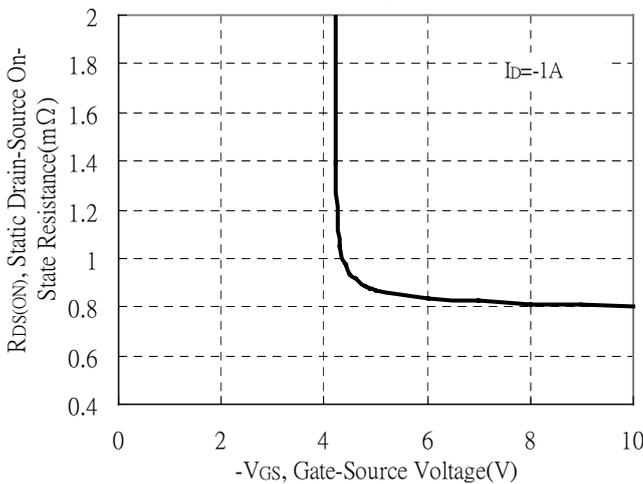
Static Drain-Source On-State resistance vs Drain Current



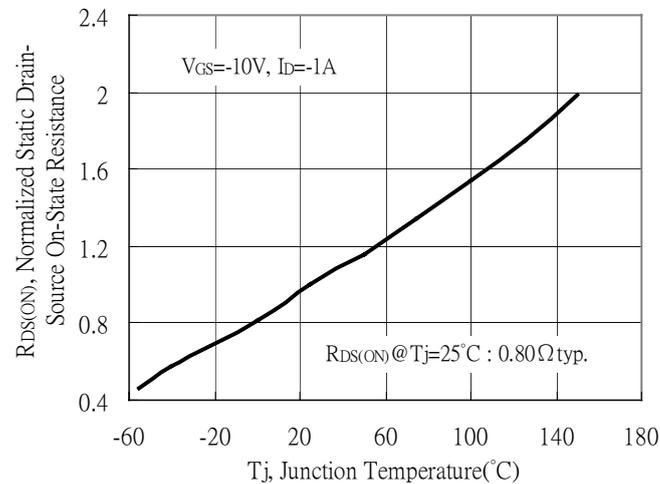
Reverse Drain Current vs Source-Drain Voltage



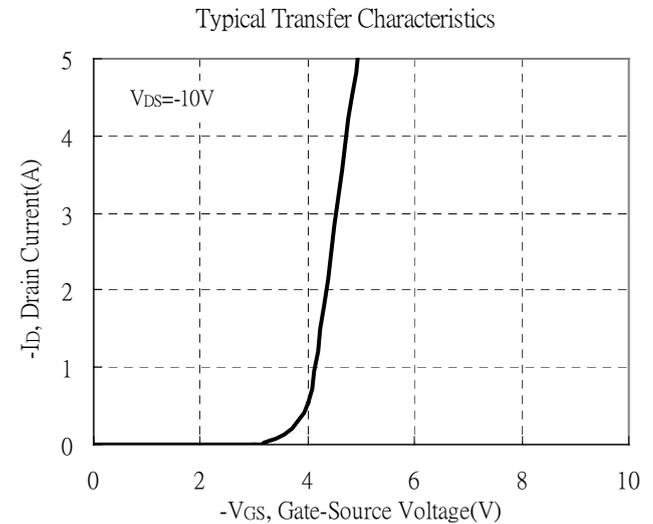
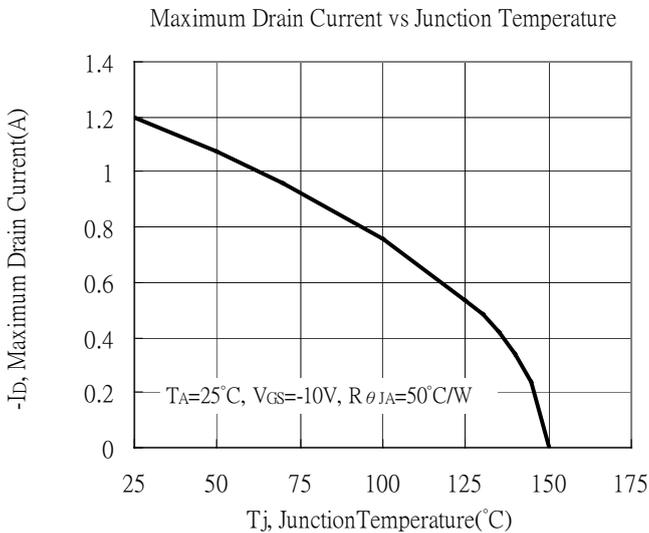
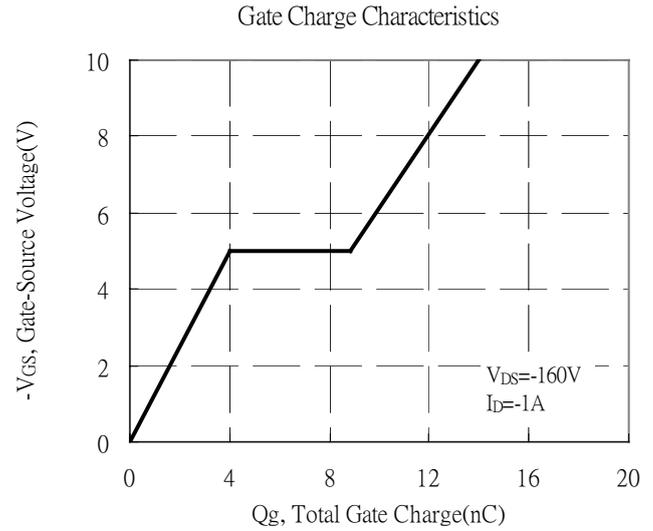
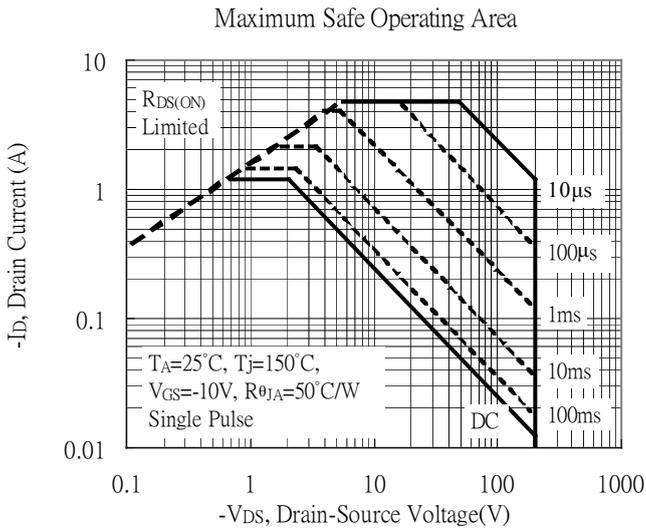
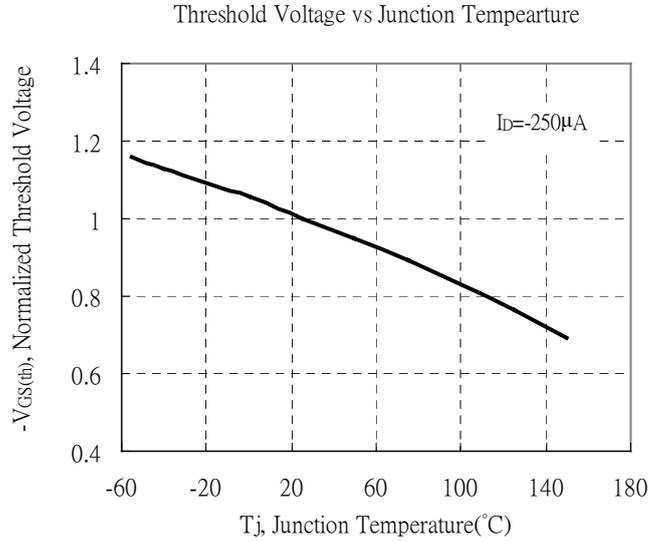
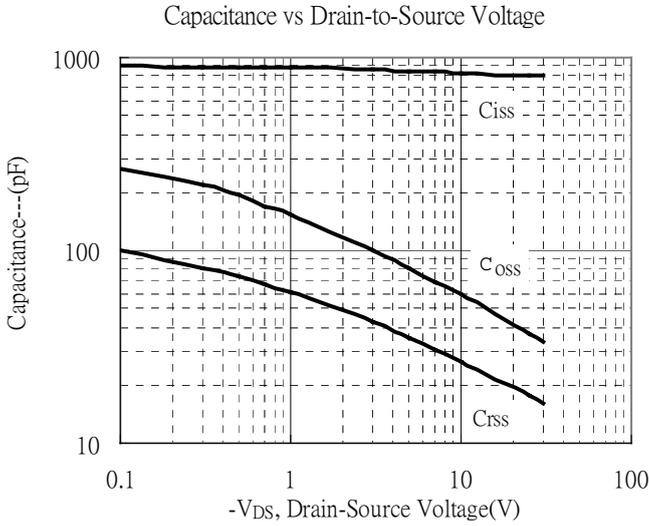
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Drain-Source On-State Resistance vs Junction Temperature

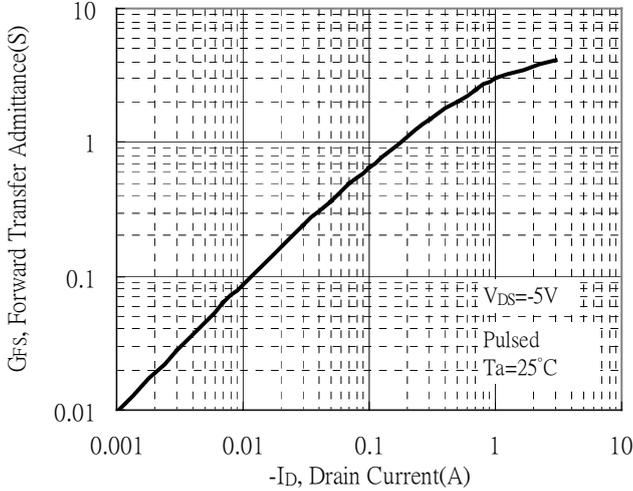


**Typical Characteristics(Cont.)**

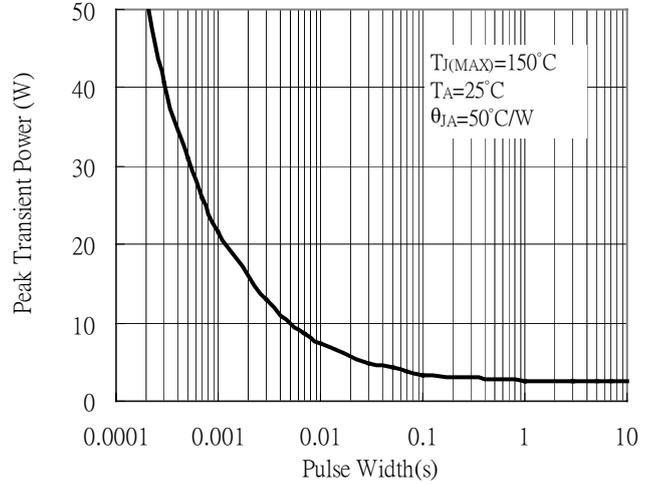


**Typical Characteristics(Cont.)**

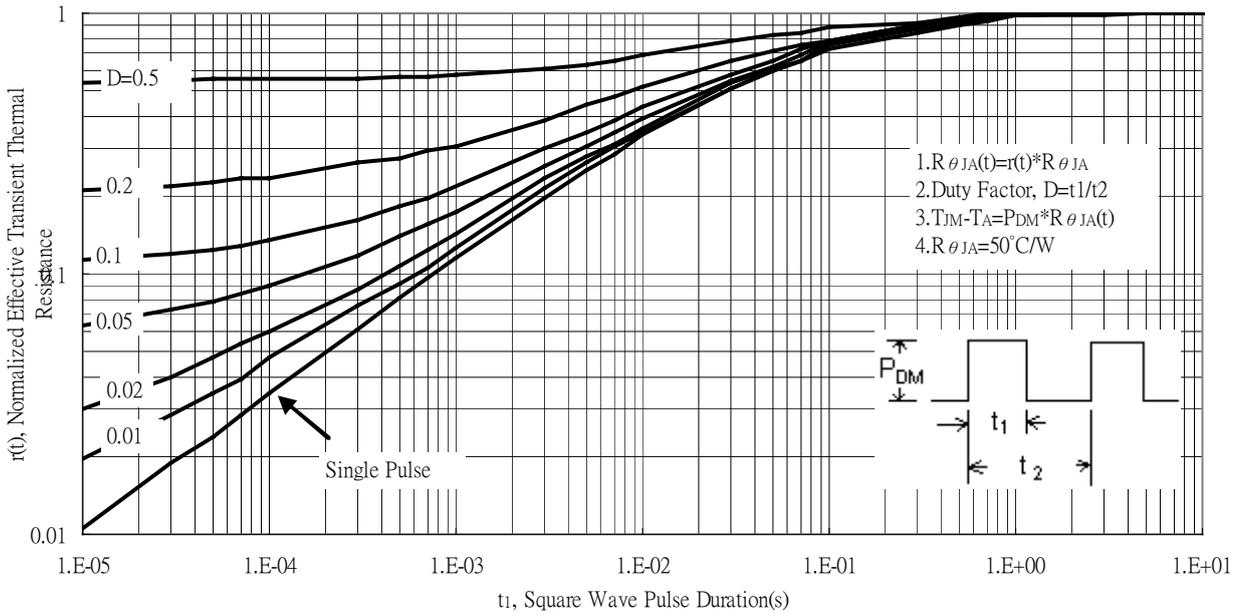
Forward Transfer Admittance vs Drain Current



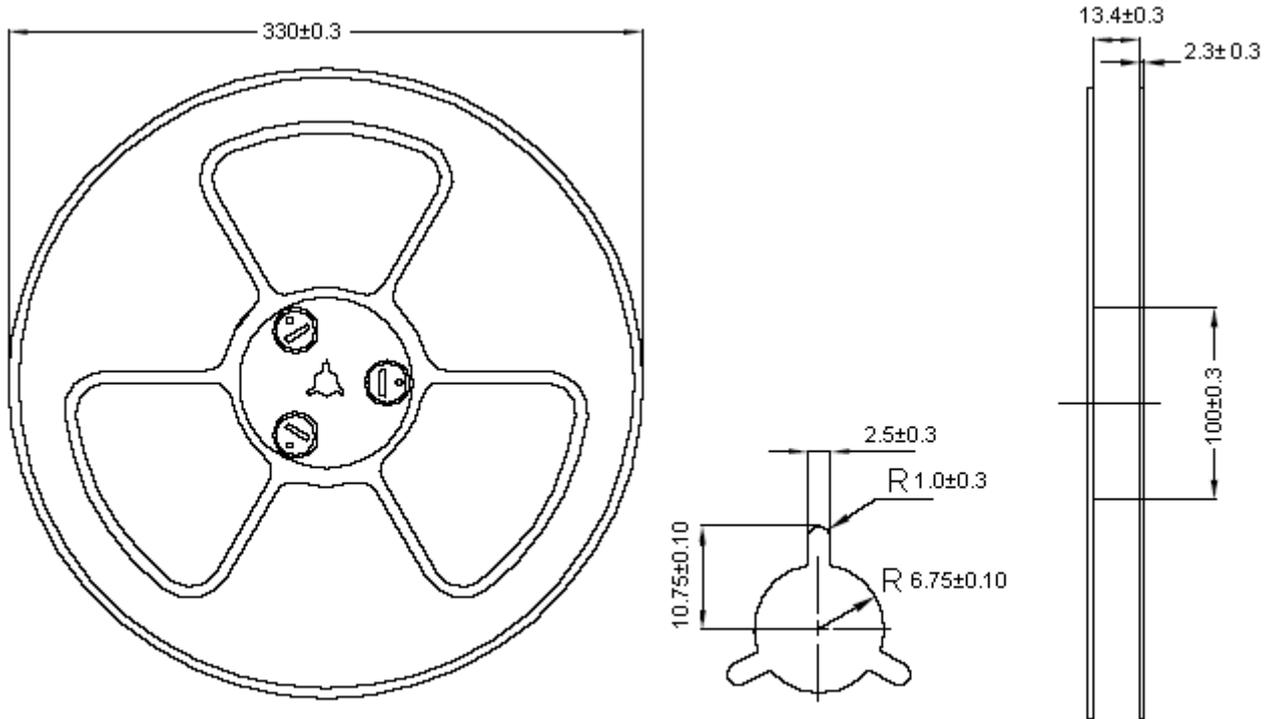
Single Pulse Maximum Power Dissipation



Transient Thermal Response Curves



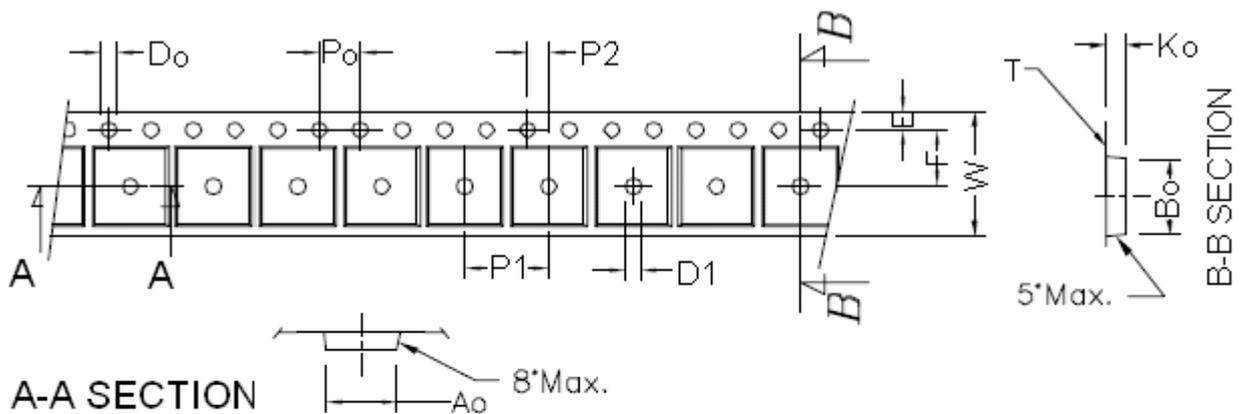
**Reel Dimension**



UNIT : mm

NOTE : 1. Material : Anti-static polystyrene  
 2. Surface resistivity  $10^9 \Omega/\text{sq}$

**Carrier Tape Dimension**

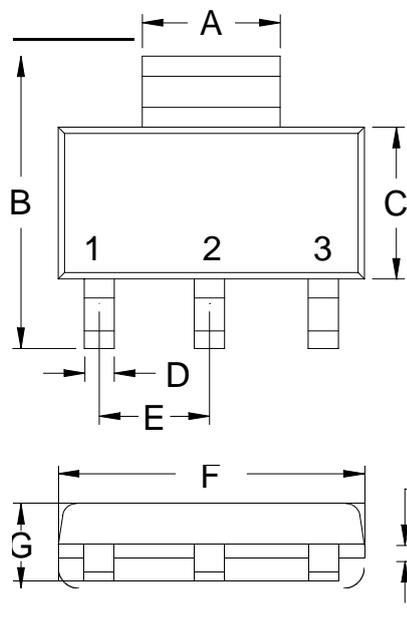


**A-A SECTION**

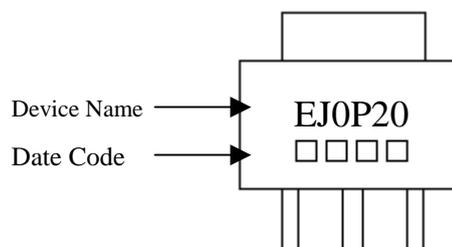
Symbol	Ao	Bo	Ko	Po	P1	P2	T
Spec	6.83±0.1	7.42±0.1	1.88±0.1	4.0±0.1	8.0±0.10	2.0±0.05	0.292±0.02
Symbol	E	F	Do	D1	W	10Po	
Spec	1.75±0.1	5.5±0.05	1.60±0.1	1.5±0.25	12 <sup>+0.3</sup> <sub>-0.1</sub>	40.0±0.2	

Unit : mm

**SOT-223 Dimension**



Marking:



Style: Pin 1.Gate 2.Drain 3.Source

3-Lead SOT-223 Plastic Surface Mounted Package

\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.23	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					